



BDV64-A-B-C

PNP SILICON DARLINGTONS POWER TRANSISTORS

They are silicon epitaxial base transistors mounted in TO-3PN.
 Theyare designed for audio output stages and general amplifier and switching applications.
 complementary is BDV65-A-B-C
 Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
V_{CEO}	Collector-Emitter Voltage	BDV64	-60	V
		BDV64A	-80	
		BDV64B	-100	
		BDV64C	-120	
V_{CBO}	Collector-Base Voltage	BDV64	-60	V
		BDV64A	-80	
		BDV64B	-100	
		BDV64C	-120	
V_{EBO}	Emitter-Base Voltage	BDV64	-5.0	V
		BDV64A		
		BDV64B		
		BDV64C		
I_C	Collector Current	BDV64	-12	A
		BDV64A		
		BDV64B		
		BDV64C		
I_{CM}	Collector Peak Current	BDV64	-15	A
		BDV64A		
		BDV64B		
		BDV64C		
I_B	Base Current	BDV64	-0.5	A
		BDV64A		
		BDV64B		
		BDV64C		



BDV64-A-B-C

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings			Value	Unit
P _T	Power Dissipation	T _{mb} = 25°C	BDV64	125	W
			BDV64A		
			BDV64B		
			BDV64C		
		T _{mb} = 25°C	BDV64	3.5	
			BDV64A		
			BDV64B		
			BDV64C		
T _J	Junction Temperature	BDV64	150	°C	
		BDV64A			
		BDV64B			
		BDV64C			
T _s	Storage Temperature	BDV64	-65 to +150		
		BDV64A			
		BDV64B			
		BDV64C			

THERMAL CHARACTERISTICS

Symbol	Ratings		Value	Unit
R_{thj-c}	Thermal Resistance, Junction to Case	BDV64	1	$^{\circ}\text{C} / \text{W}$
		BDV64A		
		BDV64B		
		BDV64C		
R_{thj-a}	Thermal Resistance, Junction to Ambient	BDV64	35.7	
		BDV64A		
		BDV64B		
		BDV64C		

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ELECTRICAL CHARACTERISTICS

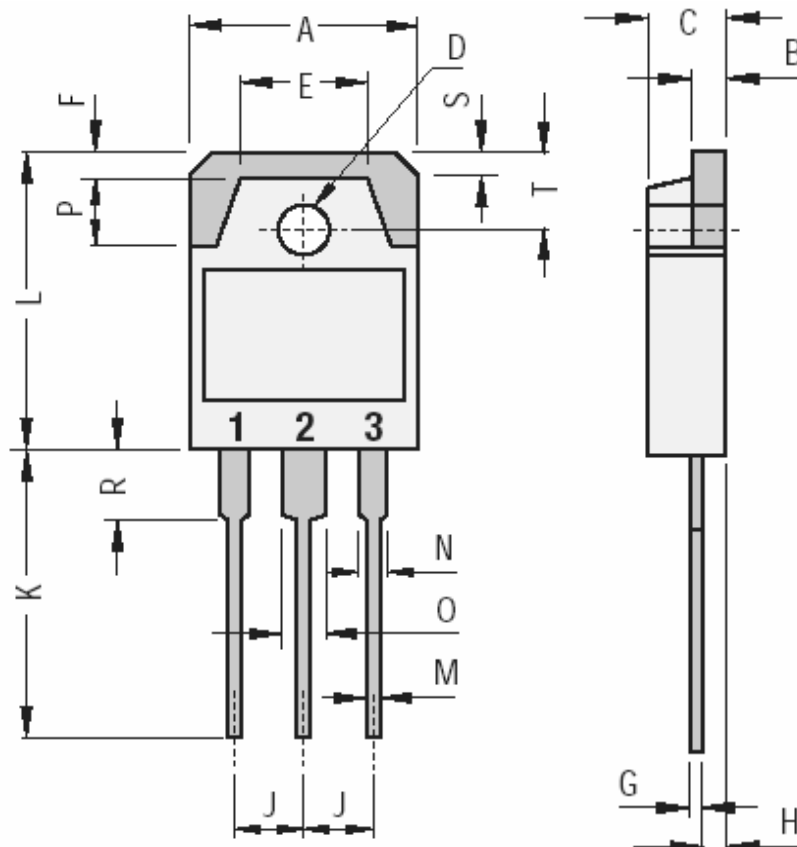
TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Typ	Max	Unit	
I _{CEO}	Collector Cutoff Current	V _{CE} = -30 V, I _B = 0		-	-	-2	mA	
		V _{CE} = -40 V, I _B = 0						
		V _{CE} = -50 V, I _B = 0						
		V _{CE} = -60 V, I _B = 0						
I _{EBO}	Emitter Cutoff Current	V _{BE} = -5 V, I _C = 0		-	-	-5	mA	
I _{CBO}	Collector Cutoff Current	I _E = 0 T _J =25°C	V _{CB} = -60 V	BDV64	-	-	-0.4	mA
			V _{CB} = -80 V	BDV64A				
			V _{CB} = -100 V	BDV64B				
			V _{CB} = -120 V	BDV64C				
		I _E = 0 T _J =150°C	V _{CB} = -30 V	BDV64	-	-	-2	
			V _{CB} = -40 V	BDV64A				
			V _{CB} = -50 V	BDV64B				
			V _{CB} = -60 V	BDV64C				
V _{CEO}	Collector-Emitter Breakdown Voltage (*)	I _C = -30 mA, I _B = 0		BDV64	-60	-	-	V
				BDV64A	-80	-	-	
				BDV64B	-100	-	-	
				BDV64C	-120	-	-	
h _{FE}	DC Current Gain (*)	V _{CE} = -4 V, I _C = -5 A		BDV64	1000	-	-	-
				BDV64A				
				BDV64B				
				BDV64C				
V _{CE(SAT)}	Collector-Emitter saturation Voltage (*)	I _C = -5 A, I _B = -20 mA		BDV64	-	-	-2	V
				BDV64A				
				BDV64B				
				BDV64C				
V _{BE}	Base-Emitter Voltage(*)	V _{CE} = -4 V, I _C = -5 A		BDV64	-	-	-2,5	V
				BDV64A				
				BDV64B				
				BDV64C				

(*) Pulse Width $\approx 300 \mu\text{s}$, Duty Cycle $\angle 1.5 \%$

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MECHANICAL DATA CASE TO3PN Non Isolated Plastic Package



DIMENSIONS (mm)		
	Min.	Max.
A	15.20	16.00
B	1.90	2.10
C	4.60	5.00
D	3.10	3.30
E		9.60
F		2.00
G	0.35	0.55
H		1.40
J	5.35	5.55
K	20.00	
L	19.60	20.20
M	0.95	1.25
N		2.00
O		3.00
P		4.00
R		4.00
S		1.80
T	4.80	5.20

Pin 1 :	Base
Pin 2 :	Collector
Pin 3 :	Emitter
Package	Collector

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